ABSTRACT OF THE DISCLOSURE

A solid-state imaging device includes a plurality of vertical charge transferring portions, and a horizontal charge transferring portion connected to at least one end of the vertical charge transferring portion. A vertical transfer channel region of a first conductivity, an element separating region of a second conductivity and a vertical well region of the second conductivity that constitute the vertical charge transferring portion are extended up to the connection portion between the vertical charge transferring portions and the horizontal charge transferring portion, and the end portions of the extended regions of the vertical transfer channel region of the first conductivity and the vertical well region of the second conductivity on the side of the horizontal charge transferring portion are positioned more on the side of the horizontal charge transferring portion than the end portion of the final vertical transfer electrode on the side of the horizontal charge transferring portion, and are positioned within 1.5 μm from the end portion of the element separating region of the second conductivity on the side of the horizontal charge transferring portion.